

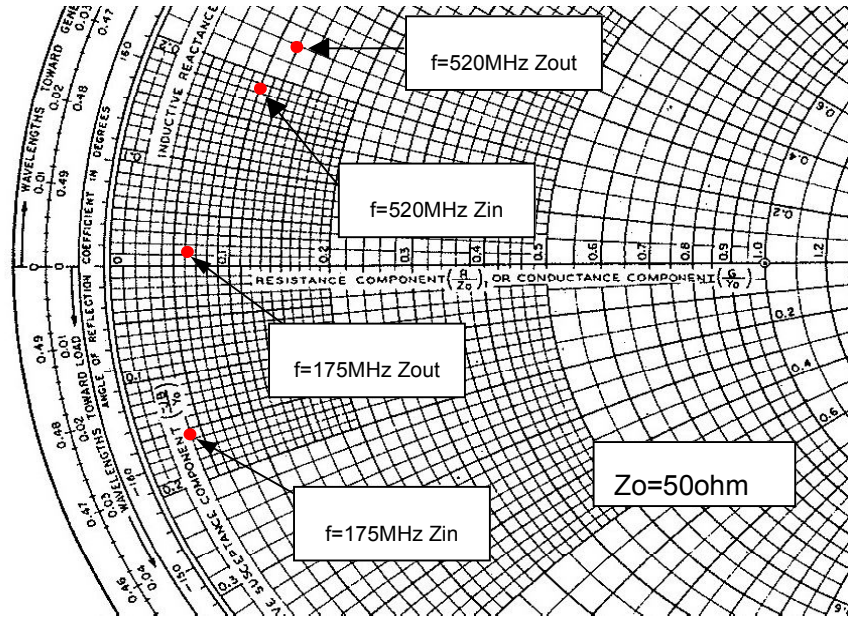
**ELECTROSTATIC SENSITIVE DEVICE**  
OBSERVE HANDLING PRECAUTIONS

**MITSUBISHI RF POWER MOS FET**

# RD15HVF1

**RoHS Compliance, Silicon MOSFET Power Transistor, 175MHz520MHz,15W**

## INPUT/OUTPUT IMPEDANCE VS.FREQUENCY CHARACTERISTICS



$Z_{in}$  ,  $Z_{out}$

f (MHz)	$Z_{in}$ (ohm)	$Z_{out}$ (ohm)	Conditions
175	$2.34-j8.01$	$3.06+j0.74$	$P_o=15W$ , $V_{dd}=12.5V$ , $P_{in}=0.6W$
520	$5.42+j9.22$	$6.02+j12.34$	$P_o=15W$ , $V_{dd}=12.5V$ , $P_{in}=3.0W$